# BTA316-800B0



3Q Hi-Com Triac
Rev. 1 — 1 November 2011

**Objective data sheet** 

### 1. **Product profile**

### 1.1 General description

Planar passivated high commutation three quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in circuits where high static and dynamic dV/dt and high dI/dt can occur. This "series B0" triac will commutate the full RMS current at the maximum rated junction temperature without the aid of a snubber.

### 1.2 Features and benefits

- 3Q technology for improved noise immunity
- High immunity to false turn-on by dV/dt
- High minimum gate trigger current for guaranteed immunity to gate noise
- High voltage capability

- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only
- Very high commutation capability with maximum false trigger immunity

## 1.3 Applications

- Electronic thermostats (heating and cooling)
- High power motor controls e.g. washing machines and vacuum cleaners
- Rectifier-fed DC inductive loads e.g. DC motors and solenoids
- Refrigeration and air conditioning compressors



### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage	e	-	-	800	V
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	-	140	Α
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 101 °C; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	-	16	Α
Static cha	racteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$	10	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$	10	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_i = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{\text{Figure 7}}$	10	-	50	mA

# 2. Pinning information

**Table 2.** Pinning information

I GOIO E.		Thining information						
Pin	Symbol	Description	Simplified outline	Graphic symbol				
1	T1	main terminal 1		<b>.</b> .				
2	T2	main terminal 2	mb	T2T1				
3	G	gate		sym051				
3 mb	T2	mounting base; main terminal 2	1 2 3					
			SOT78 (TO-220AB)					

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BTA316-800B0	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

BTA316-800B0

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 101 °C; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	16	Α
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25  ^{\circ}C$ ; $t_p = 20  ms$ ; see Figure 4; see Figure 5	-	140	Α
		full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 16.7 \text{ ms}$	-	150	Α
I <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; sine-wave pulse	-	98	$A^2s$
dI <sub>T</sub> /dt	rate of rise of on-state current	$I_T = 20 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A/}\mu\text{s}$	-	100	A/µs
I <sub>GM</sub>	peak gate current		-	2	Α
P <sub>GM</sub>	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
T <sub>j</sub>	junction temperature		-	125	°C

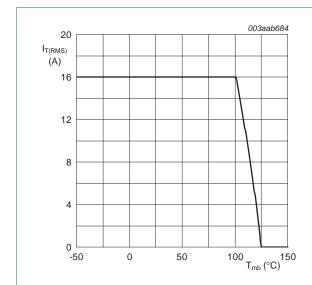
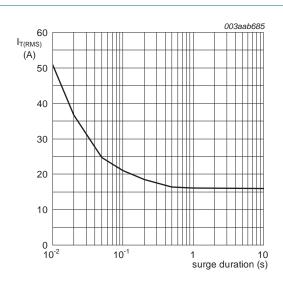


Fig 1. RMS on-state current as a function of mounting base temperature; maximum values



f = 50 Hz;  $T_{mb}$  = 101 °C

Fig 2. RMS on-state current as a function of surge duration; maximum values

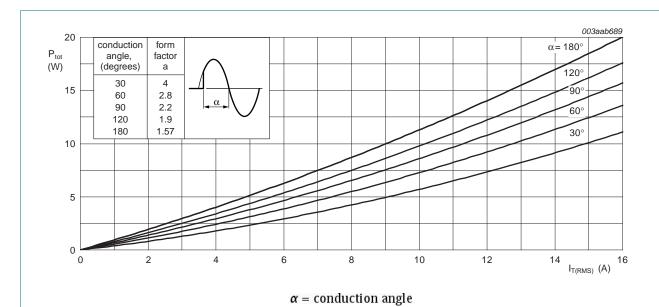


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values

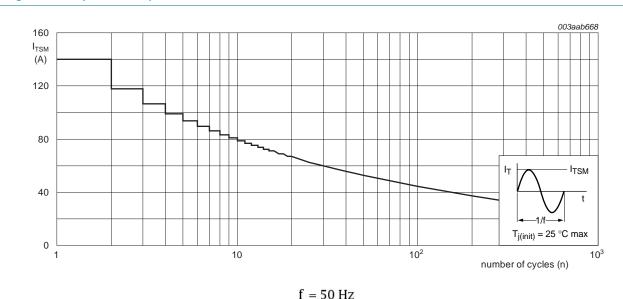
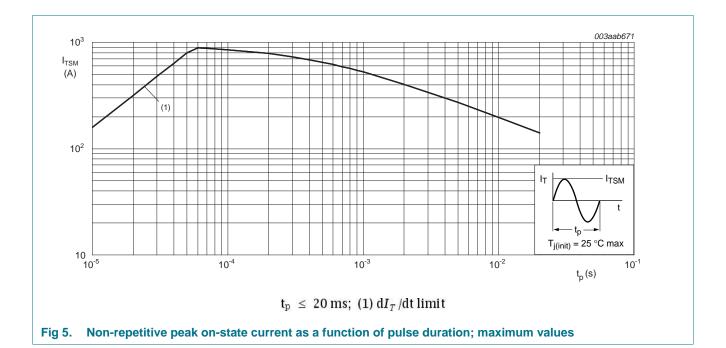


Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



# 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to	full cycle; see Figure 6	-	-	1.2	K/W
	mounting base	half cycle; see Figure 6	-	-	1.7	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

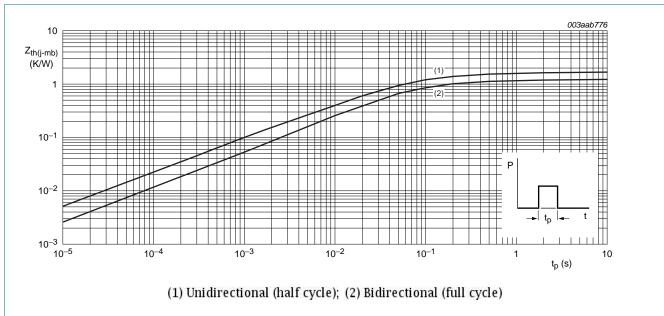
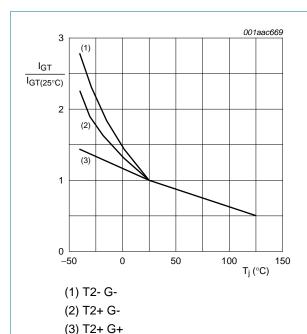


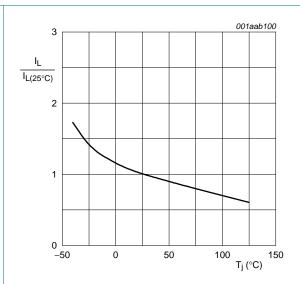
Fig 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

# 6. Characteristics

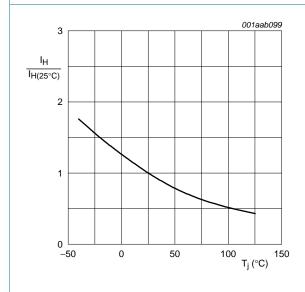
Table 6. Characteristics

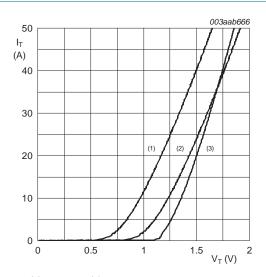
Table 0.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{\text{Figure 7}}$	10	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2 + G-;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$	10	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G-};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{\text{ Figure 7}}$	10	-	50	mA
I <sub>L</sub>	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{\text{ Figure 8}}$	-	-	60	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{}$	-	-	90	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{\text{ Figure 8}}$	-	-	60	mA
I <sub>H</sub>	holding current	$V_D = 12 \text{ V; } T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{}$	-	-	60	mΑ
$V_{T}$	on-state voltage	$I_T = 18 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 10}{}$	-	1.3	1.5	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ see Figure 11	-	0.8	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ see Figure 11	0.25	0.4	-	V
I <sub>D</sub>	off-state current	$V_D = 800 \text{ V}; T_j = 125 ^{\circ}\text{C}$	-	0.1	0.5	mΑ
Dynamic	characteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_j$ = 125 °C; exponential waveform; gate open circuit	1000	-	-	V/µs
dI <sub>com</sub> /dt	rate of change of commutating current	$V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 16 A; $dV_{com}/dt$ = 10 V/ $\mu$ s; gate open circuit	20	-	-	A/ms
t <sub>gt</sub>	gate-controlled turn-on time	$I_{TM} = 20 \text{ A}; V_D = 800 \text{ V}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs





- Fig 7. Normalized gate trigger current as a function of junction temperature
- Fig 8. Normalized latching current as a function of junction temperature





 $V_0 = 1.024 \text{ V}$ 

 $R_s = 0.021 \Omega$ 

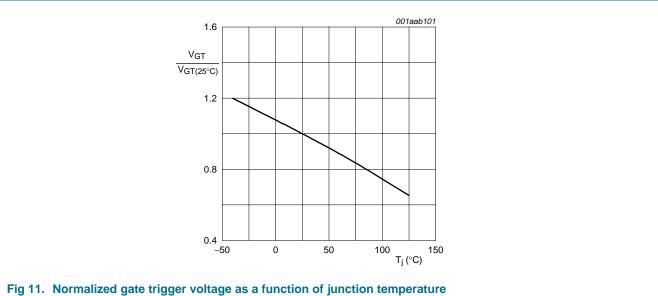
(1) T<sub>j</sub> = 125 °C; typical values

(2)  $T_j = 125$  °C; maximum values

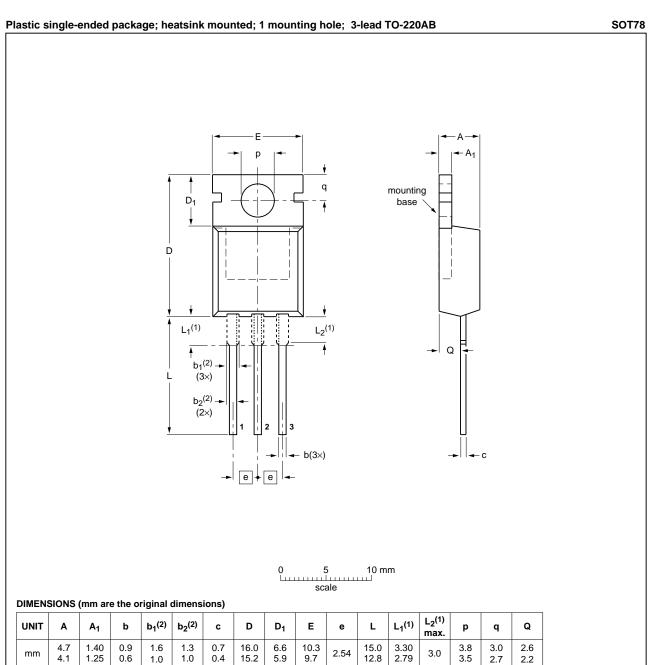
(3) T<sub>j</sub> = 25 °C; maximum values

Fig 9. Normalized holding current as a function of junction temperature

Fig 10. On-state current as a function of on-state voltage



# Package outline



- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE VERSION		REFER	ENCES	EUROPEAN ISSUE DAT	ISSUE DATE
	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46		<del>08-04-23</del> 08-06-13

Fig 12. Package outline SOT78 (TO-220AB)

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# 8. Revision history

# Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA316-800B0 v.1	20111101	Objective data sheet	-	-

# 9. Legal information

### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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